

FPT320

High Sensitivity Silicon Phototransistors

Description

PACKAGE FPT320

OPTO-26

The FPT320 is a silicon nitride protected NPN Planar phototransistor with exceptionally stable characteristics and high illumination-sensitivity. The case is made of a special plastic compound with transparent resin encapsulation.

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature -55° C to 100° C
Operating Temperature -55° C to 85° C
Pin Temperature (Soldering, 5 s)
Relative Humdity at 65° C
85%

Power Dissipation (Note 1)

Total Dissipation at T_C = 25° C 200 mW Derate Linearly from 25° C 3.33 mW/° C Total Dissipation at T_A = 25° 100 mW Derate Linearly from 25° C 1.67 mW/° C

Voltages & Current

V_{CE (sus)} Collector to Emitter Voltage 20 V I_C Collector Current 25 mA

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 7)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
I _{CE(It)}	Photo Current, GaAs Source (Note 3)	0.7		mA	$V_{CE} = 5.0 \text{ V}, H = 1 \text{ mW/cm}^2$
I _{CEO}	Collector Dark Current (Note 4)		100	nA	$V_{CE} = 5.0 \text{ V}$
V _{CEO(sus)}	Collector to Emitter Sustaining Voltage (Note 4)	20		٧	I _C = 1.0 mA (pulsed)
V _{CE(sat)}	Collector to Emitter Saturation Voltage, Tungsten Source (Note 2)		0.55	V	$I_C = 1.0 \text{ mA}, H = 20 \text{ mW/cm}^2$

NOTES:

- 1. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 2. Measured at noted irradiance as emitted from a tungsten filament lamp at a color temperature of 2854° K.
- 3. These are values obtained at noted irradiance as emitted from a GaAs source at 99 nm.
- 4. Measured with radiation flux intensity of less than 0.1 μ W/cm² over the spectrum from 100-1500 nm.
- 5. Same electrical characteristics as FPT120 except for Icem.
- 6. Same electrical characteristics as FPT130 except for Iceim.
- 7. For product family characteristic curves, refer to Curve Set FPT120.